

N-channel 40 V, 14 mΩ logic level MOSFET in LFPAK33 13 May 2016

**Product data sheet** 

#### 1. **General description**

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. Features and benefits

- Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V<sub>GS(th)</sub> rating of greater than 0.5 V at 175 °C

#### Applications 3.

- 12 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching •

#### Quick reference data 4.

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	44	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	55	W
Static charact	eristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	11	14	mΩ
Dynamic char	acteristics					
Q <sub>GD</sub>	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$	-	4.8	-	nC

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source		G C C C C C C C C C C C C C C C C C C C
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

### 6. Ordering information

Table 3. Ordering int	formation					
Type number	Package					
	Name	Description	Version			
BUK9M14-40E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9M14-40E	91440E

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

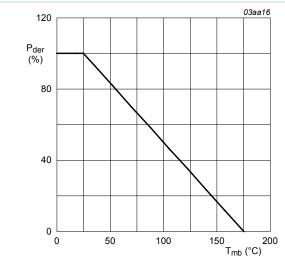
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	40	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	10	V
		Pulsed; T <sub>j</sub> ≤ 175 °C	[1][2]	-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	55	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	44	А
		V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	31	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 3		-	176	А

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Symbol	Parameter	Conditions		Min	Мах	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
l <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	44	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	176	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} & I_{D} = 44 \; A;  V_{sup} \leq 40 \; V; \; R_{GS} = 50 \; \Omega; \\ & V_{GS} = 5 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped; \\ & \overline{Fig. 4} \end{split}$	[3][4]	-	25.9	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm. Significantly longer life times are achieved by lowering  $\rm T_{j}$  and or  $\rm V_{GS}$ [1]
- [2]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]
- Refer to application note AN10273 for further information. [4]





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

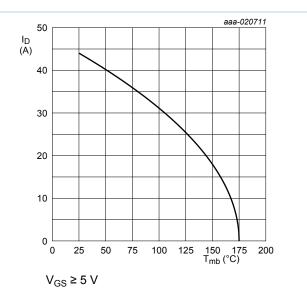
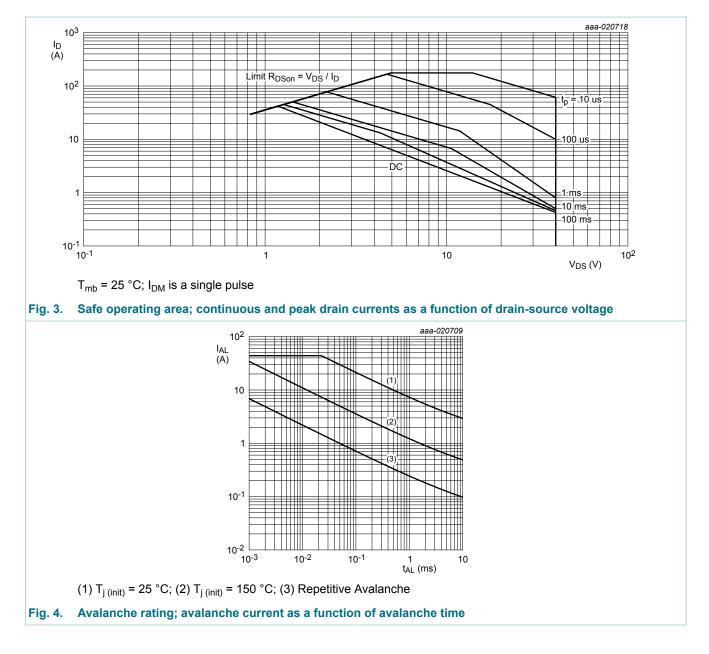


Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 44A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

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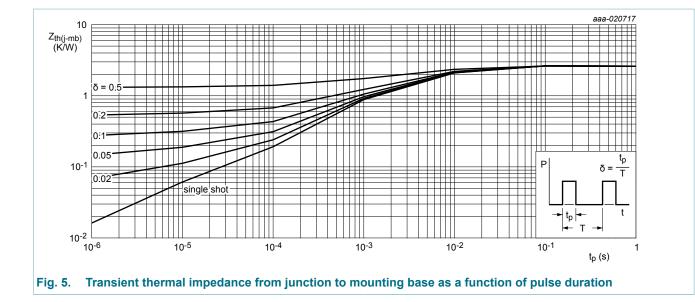


### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	2.46	2.75	K/W

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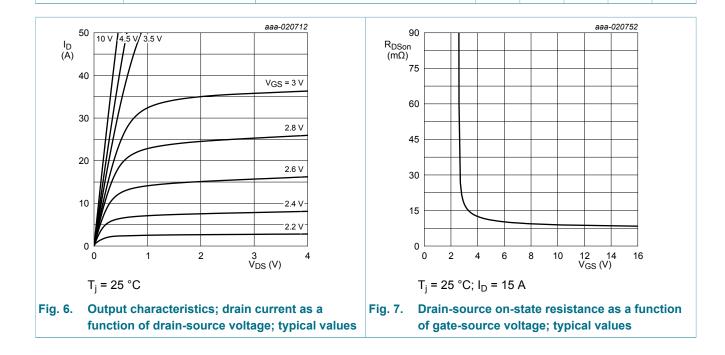
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·	I			_
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	-	-	V
V <sub>GS(th)</sub> gate-source threshold voltage	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; Fig. 10	,	-	-	2.45	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.01	10	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	11	14	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	8.9	11	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; Fig. 12	-	-	28	mΩ
Dynamic ch	aracteristics	· · · ·	1			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 5 V;	-	11.3	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	2.4	-	nC

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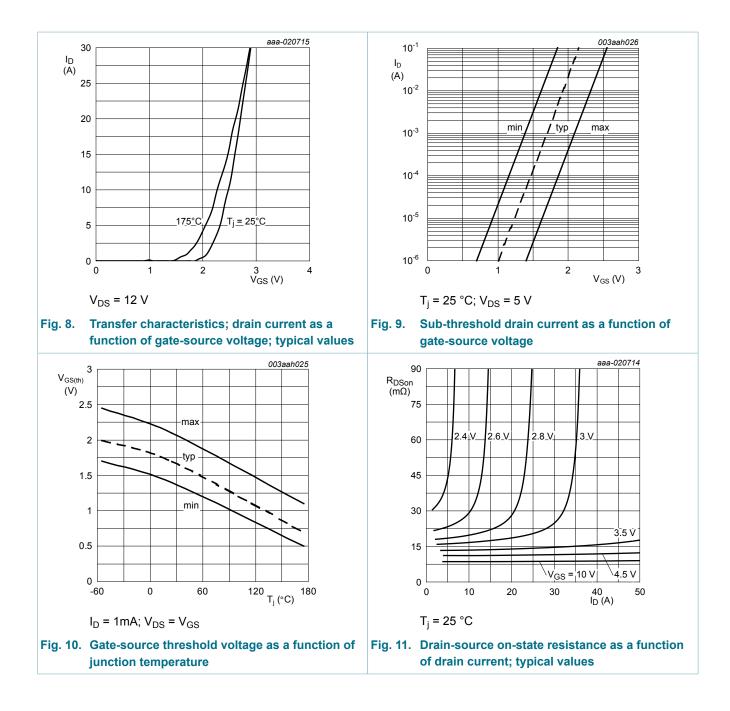
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Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
Q <sub>GD</sub>	gate-drain charge		-		4.8	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 25 V; $V_{GS}$ = 0 V; f = 1 MHz;	-		911	1211	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-		152	182	pF
C <sub>rss</sub>	reverse transfer capacitance		-		91	125	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 2 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega; \text{ T}_{j} = 25 ^{\circ}\text{C}$	-		7.4	-	ns
t <sub>r</sub>	rise time		-		13.2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-		16.5	-	ns
t <sub>f</sub>	fall time		-		12.2	-	ns
Source-dra	in diode						_
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-		0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 15 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-		17.7	-	ns
Qr	recovered charge	V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C	-		9.2	-	nC



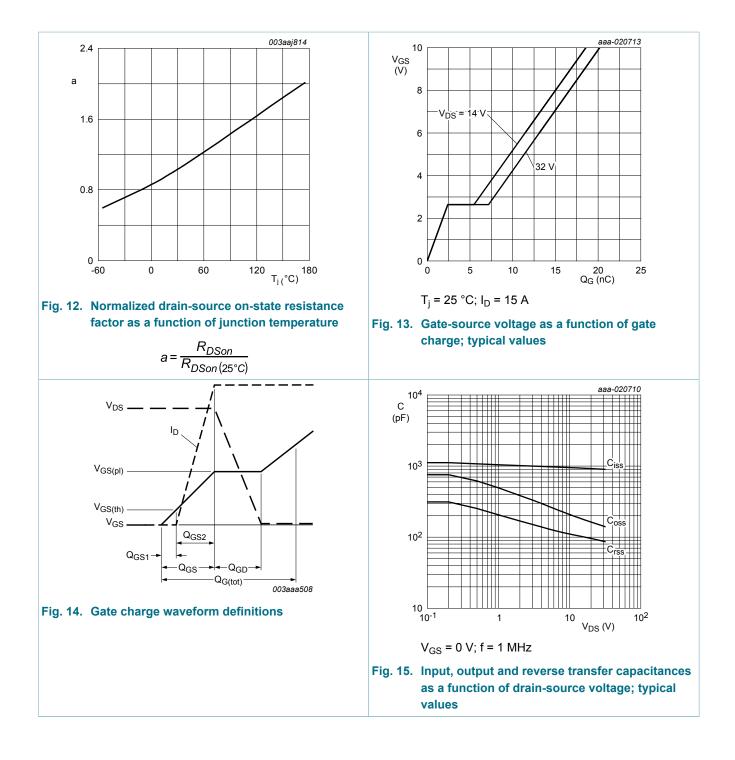
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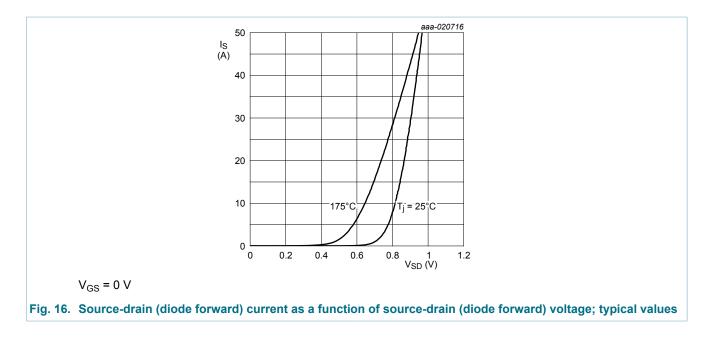
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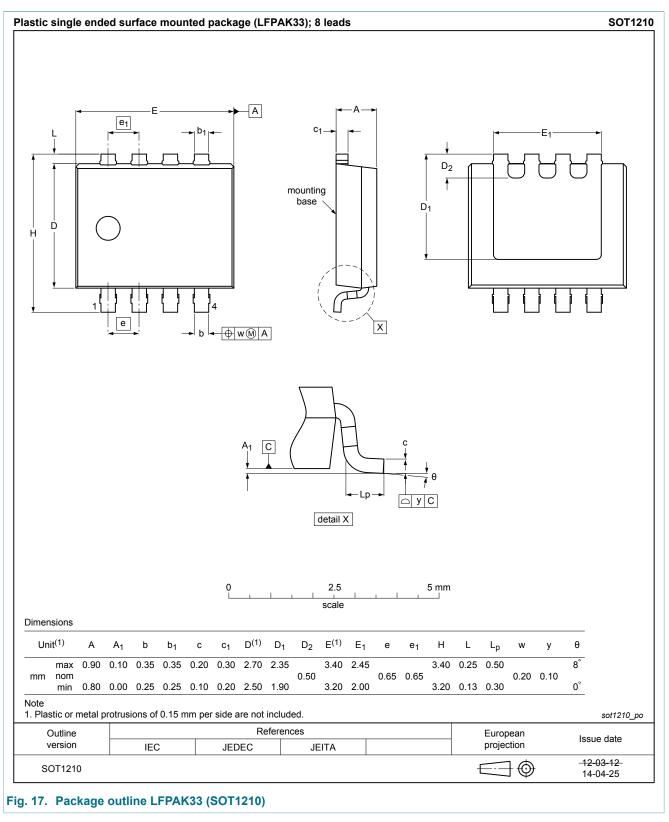


# **11. Application information**

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

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### 12. Package outline



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#### N-channel 40 V, 14 mΩ logic level MOSFET in LFPAK33

### 13. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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#### N-channel 40 V, 14 m $\Omega$ logic level MOSFET in LFPAK33

### 14. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Application information	9
12	Package outline	10
13	Legal information	11
13.1	Data sheet status	
13.2	Definitions	11
13.3	Disclaimers	11
13.4	Trademarks	

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